

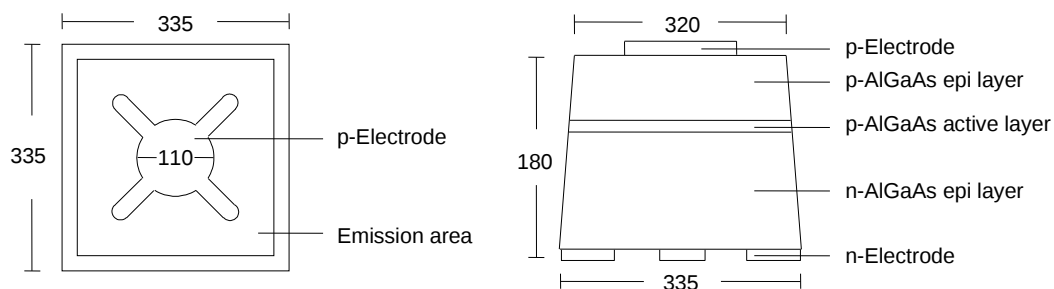
■ Features :

- AlGaAs/AlGaAs Wafer
- Very High Power
- High Performance
- Superior Thermal Stability

■ Typical Applications :

- IrDA
- Encoder
- Data Communication

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	335 μm x 335 μm
	Thickness	180 $\pm$ 50 μm
	Emission area	320 μm
	Bonding pad	110 μm
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Smooth	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 50 \text{ mA}$	-	1.70	2.00	V
		$I_F = 200 \text{ mA}$	-	2.20	3.00	
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_P	$I_F = 50 \text{ mA}$	-	770	-	nm
Spectral width at half height	$\Delta \lambda$	$I_F = 50 \text{ mA}$	-	40	-	nm
Radiant Power	P_o	$I_F = 20 \text{ mA}$	1.50	2.10	-	mW
Rise / Fall Time	t_r / t_f	$I_F = 50 \text{ mA}$	-	15 / 10	-	ns

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

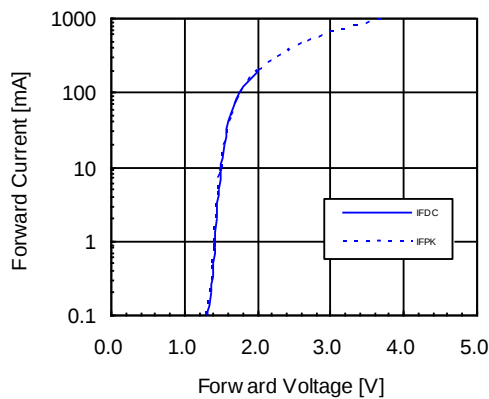


Fig 2. Relative Radiant Power vs. Forward Current

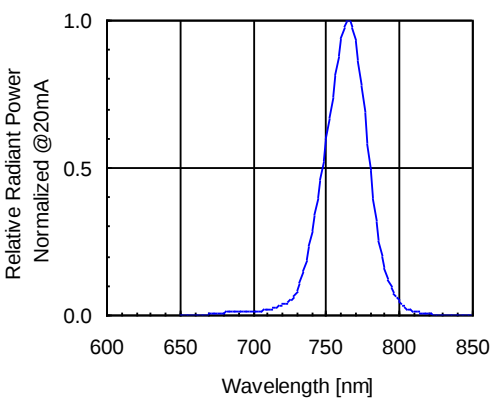


Fig 3. Relative Radiant Power vs. Forward DC Current

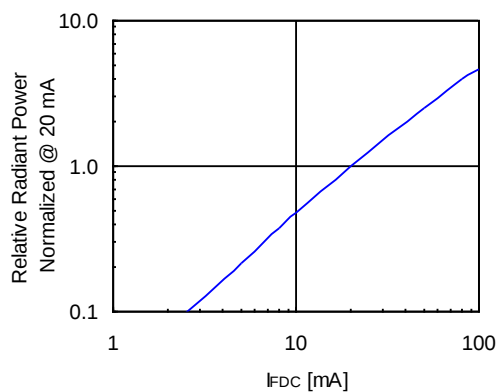


Fig 4. Relative Radiant Power vs. Forward Peak Current

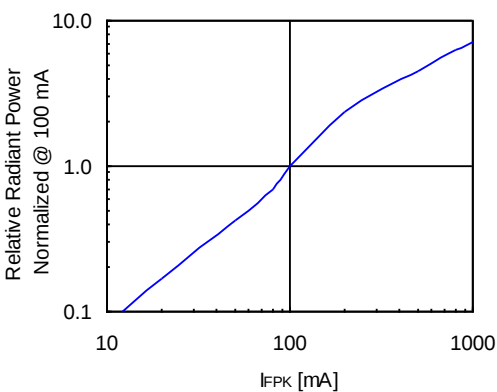


Fig 5. Forward DC Voltage vs. Temperature

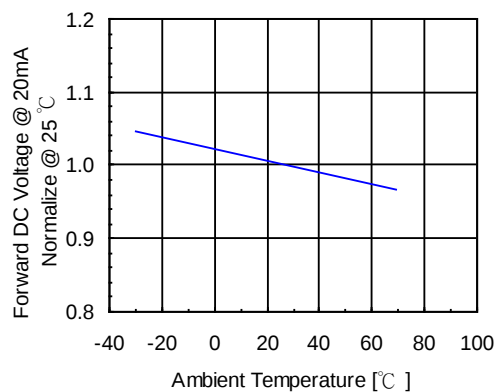


Fig 6. Relative Radiant Power vs. Temperature

